

PHASE CHANGEABLE MEMORY DEVICES AND METHODS FOR
FABRICATING THE SAME

Abstract of the Disclosure

Phase-changeable memory devices and method of fabricating phase-changeable memory devices are provided that include a phase-changeable material pattern of a phase-changeable material that includes nitrogen atoms. First and second electrodes are electrically connected to the phase-changeable material pattern and provide an electrical signal thereto. The phase-changeable material pattern may have a polycrystalline structure.